

In the Claims:

1 (cancelled). Process for the metallization of at least one insulating layer of an electronic or microelectronic component, whose layer thickness is at most 50 Fm, wherein firstly

- at least one insulating layer is applied to the substrate and is activated by treatment with an activator,
- then another insulating layer is applied and patterned, and lastly
- the first insulating layer is seeded and metallized.

2 (cancelled). Process according to Claim 1, in which the two insulating layers are of the same material.

3 (cancelled). Process according to Claim 1 or 2, in which the first insulating layer is patterned before the second insulating layer is applied.

4 (currently amended). A process for metallizing at least one insulating layer of an electronic or microelectronic component, which comprises:

applying at least one first insulating layer to a substrate such that the first insulating layer has a thickness not greater than 50 μ m;

activating all of the first insulating layer by treatment with an activator;

then applying and patterning a second insulating layer made of a photosensitive material; and

then seeding and metallizing regions of the first insulating layer that are exposed by the patterning step.

5 (previously presented). The process according to claim 4, which comprises forming the first insulating layer and the second insulating layer from the same material.

6 (previously presented). The process according to claim 5, which comprises patterning the first insulating layer before the second insulating layer is applied.

7 (previously presented). The process according to claim 4, which comprises patterning the first insulating layer before the second insulating layer is applied.